

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|---|------|-----|--------|---|--|---------------------|
| 1 | BRS | L1 | 4741 | dummy near2 pattern\$4 | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 2 | BRS | L2 | 69526 | dummy | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 3 | BRS | L3 | 1946 | dummy near2 wir\$6 | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 4 | BRS | L4 | 448201 | wiring patterns near4 (gate adj electrode) | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 5 | BRS | L5 | 3730 | (wiring patterns near4 (gate adj electrode)) same dummy | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|-------|--|--|---------------------|
| 6 | BRS | L6 | 867 | ((wiring patterns near4 (gate adj electrode)) same dummy) and @ad<"19930716" | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 7 | BRS | L7 | 219 | (signal near2 wiring) and (power adj source adj wiring) | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 8 | BRS | L8 | 56178 | wiring near4 pattern\$6 | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 9 | BRS | L9 | 70106 | dummy | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 10 | BRS | L10 | 70106 | dummy or dummies | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |

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|----|------|-----|-------------|---|--|---------------------|
| 11 | BRS | L11 | 1288 | (dummy or dummies) near2 wiring | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/19 16:39 |
| 12 | BRS | L12 | 627 | (wiring near4 pattern\$6) and ((dummy or dummies) near2 wiring) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/19 16:39 |
| 13 | BRS | L13 | 2221 | (wiring near4 pattern\$6) same level | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/19 16:39 |
| 14 | BRS | L14 | 1069 | (first adj wiring) same (second adj wiring) same (third adj wiring) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/19 16:39 |
| 15 | BRS | L15 | 164972 1 | simultaneous\$6 or concuren\$6 or "at the same time" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/19 16:39 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|------|---|--|---------------------|
| 16 | IS&R | L16 | 366 | (257/374).CCLS. | US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 17 | BRS | L17 | 61 | ((257/374).CCLS.) and (pn adj junction) | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 18 | BRS | L18 | 34 | ((257/374).CCLS.) and (pn adj junction)) and polycrystal\$6 | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 19 | BRS | L19 | 207 | separation near4 (polycrystal\$6 or poly- crystal\$6) | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|-------|---|--|---------------------|
| 20 | BRS | L20 | 14 | (separation near4 (polycrystal\$6 or poly- crystal\$6)) and (SOI or "silicon on insulat\$6") | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 21 | BRS | L21 | 34327 | (dummy or interpolcation or interpolate or auxiliary) near2 (electrode or wire or wiring or line) | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 22 | BRS | L22 | 3953 | source adj wiring | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 23 | BRS | L23 | 112 | ((dummy or interpolcation or interpolate or auxiliary) near2 (electrode or wire or wiring or line)) and (gate adj wiring) and (source adj wiring) | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 24 | BRS | L24 | 5013 | gate adj wiring | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|-------------|--|--|---------------------|
| 25 | BRS | L25 | 6271 | ((dummy or interpolcation or interpole or auxiliary) near2 (electrode or wire or wiring or line)) near4 (between or middle or intermediate or link\$6 or interpost\$6) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/19 16:39 |
| 26 | BRS | L26 | 6177 | signal adj wiring | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/19 16:39 |
| 27 | BRS | L49 | 764 | dummy adj wiring | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/19 16:39 |
| 28 | BRS | L51 | 214497 7 | (dummy or dummies or interpolation or interpolation or inter-pole or intermediat\$6 or auxiliary or temporary) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/19 16:39 |
| 29 | BRS | L52 | 63137 | ((dummy or dummies or interpolation or interpolation or inter-pole or intermediat\$6 or auxiliary or temporary)) near8 (gate or electrode) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2004/11/19 16:39 |

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|----|------|-----|-------------|--|--|---------------------|
| 30 | BRS | L53 | 47665 | wiring near2 pattern\$6 | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 31 | BRS | L54 | 735808 3 | connect\$6 or link\$6 | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 32 | BRS | L55 | 36 | (wiring near2 pattern\$6) near4 (connect\$6 or link\$6) near4 (((dummy or dummies or interpolation or inter- polation or inter-pole or intermediat\$6 or auxiliary or temporary)) near8 (gate or electrode)) | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 33 | BRS | L56 | 576415 4 | wire or wiring or line or conductive or conductor or interconnect | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|-------|--|--|---------------------|
| 34 | BRS | L58 | 54032 | (wire or wiring or line or conductive or conductor or interconnect) near4 (connect\$6 or link\$6) near4 gate | US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 35 | BRS | L59 | 21164 | ((wire or wiring or line or conductive or conductor or interconnect) near4 (connect\$6 or link\$6) near4 gate) and (@ad<"19930716") | US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 36 | BRS | L60 | 6463 | ((wire or wiring or line or conductive or conductor or interconnect) near4 (connect\$6 or link\$6) near4 gate) and (@ad<"19930716")) and ((dummy or dummies or interpolation or interpolation or inter-pole or intermediat\$6 or auxiliary or temporary)) | US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 37 | IS&R | L62 | 947 | (438/197).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|------|------------------|--|---------------------|
| 38 | IS&R | L63 | 771 | (438/200) .CCLS. | US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 39 | IS&R | L64 | 149 | (438/737) .CCLS. | US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 40 | IS&R | L65 | 129 | (438/926) .CCLS. | US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 41 | IS&R | L66 | 1030 | (438/151) .CCLS. | US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|------|--|--|---------------------|
| 42 | IS&R | L67 | 1106 | (438/585).CCLS. | US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 43 | BRS | L29 | 1 | ((first adj wiring) same (second adj wiring) same (third adj wiring)) and @ad<"19930716") and (dummy near2 pattern\$4) | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 44 | BRS | L34 | 1 | ((wiring patterns near4 (gate adj electrode)) same dummy) and @ad<"19930716") and IGFET | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 45 | BRS | L27 | 7 | ((first adj wiring) same (second adj wiring) same (third adj wiring)) and IGFET | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|------|---|--|---------------------|
| 46 | BRS | L30 | 5 | ((first adj wiring) same (second adj wiring) same (third adj wiring)) and @ad<"19930716") and dummy | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 47 | BRS | L31 | 2 | (dummy near2 wir\$6) and IGFET | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 48 | BRS | L33 | 18 | ((dummy near2 wir\$6) and MOS) and @ad<"19930716" | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 49 | BRS | L35 | 79 | ((signal near2 wiring) and (power adj source adj wiring)) and @ad<"19930716" | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 50 | BRS | L36 | 23 | ((signal near2 wiring) and (power adj source adj wiring)) and dummy | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|------|--|--|---------------------|
| 51 | BRS | L37 | 6 | ((signal near2 wiring) and (power adj source adj wiring)) and dummy) and @ad<"19930716" | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 52 | BRS | L38 | 41 | ((wiring near4 pattern\$6) same level) and ((dummy or dummies) near2 wiring) | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 53 | BRS | L39 | 87 | ((first adj wiring) same (second adj wiring) same (third adj wiring)) and (dummy or dummies) | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 54 | BRS | L40 | 42 | ((first adj wiring) same (second adj wiring) same (third adj wiring)) and (dummy or dummies)) and (gate adj electrode) | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|------|--|--|---------------------|
| 55 | BRS | L41 | 24 | (((((first adj wiring) same (second adj wiring) same (third adj wiring)) and (dummy or dummies)) and (gate adj electrode)) and (simultaneous\$6 or concuren\$6 or "at the same time")) | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 56 | BRS | L42 | 12 | ((dummy or interpolcation or interpole or auxiliary) near2 (electrode or wire or wiring or line)) and (gate adj wiring) and (source adj wiring) and (signal adj wiring) | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 57 | BRS | L43 | 20 | ((((dummy or interpolcation or interpole or auxiliary) near2 (electrode or wire or wiring or line)) near4 (between or middle or intermediate or link\$6 or interpost\$6)) and (gate adj wiring) and (source adj wiring) | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 58 | BRS | L44 | 6 | (gate adj wiring) and (((dummy or interpolcation or interpole or auxiliary) near2 (electrode or wire or wiring or line)) near4 (between or middle or intermediate or link\$6 or interpost\$6)) and (signal adj wiring) | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|------|--|--|---------------------|
| 59 | BRS | L45 | 8 | ((gate adj wiring) and (((dummy or interpolcation or interpole or auxiliary) near2 (electrode or wire or wiring or line)) near4 (between or middle or intermediate or link\$6 or interpost\$6))) and (@ad<"19930716") | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 60 | BRS | L46 | 86 | (gate adj wiring) and (((dummy or interpolcation or interpole or auxiliary) near2 (electrode or wire or wiring or line)) near4 (between or middle or intermediate or link\$6 or interpost\$6)) | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 61 | BRS | L47 | 4 | ("5483366" "5986723" "6078366" "6201584").PN. | USPAT | 2004/11/19 16:39 |
| 62 | BRS | L48 | 16 | ("4563367" "4564997" "5016564" "4960073" "5022977" "5259922" "5344536" "5156703" "5183777" "5444207" "5290382" "4298419" "5368685" "4971651" "5350710" "5378311").PN. | USPAT | 2004/11/19 16:39 |
| 63 | BRS | L50 | 24 | (dummy adj wiring) near4 "gate electrode" | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|------|--|--|---------------------|
| 64 | BRS | L57 | 5 | ((wiring near2 pattern\$6) near4 (connect\$6 or link\$6) near4 (((dummy or dummies or interpolation or inter-polation or inter-pole or intermediat\$6 or auxiliary or temporary)) near8 (gate or electrode))) and (@ad<"19930716") | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 65 | BRS | L61 | 132 | (((((wire or wiring or line or conductive or conductor or interconnect) near4 (connect\$6 or link\$6) near4 gate) and (@ad<"19930716")) and ((dummy or dummies or interpolation or inter- polation or inter-pole or intermediat\$6 or auxiliary or temporary)) and ((second! or another or addition\$6) adj wir\$6) | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |
| 66 | BRS | L28 | 219 | ((first adj wiring) same (second adj wiring) same (third adj wiring)) and @ad<"19930716" | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|------|---------------------------------|--|---------------------|
| 67 | BRS | L32 | 208 | (dummy near2 wir\$6) and MOS | US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB | 2004/11/19 16:39 |

DERWENT-ACC-NO: 1992-160403

DERWENT-WEEK: 199907

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TITLE: Semiconductor memory device for mfg. computer
DRAM - comprises semiconductor substrate, memory cell
array region having memory cells with transistor and
capacitor, peripheral circuit etc.

----- KWIC -----

Basic Abstract Text - ABTX (1):

A semiconductor memory device is formed on a semiconductor substrate (1) and has at least one memory cell array region, in which a multiplicity of memory cells is formed, each of which has a transistor (20) and a capacitor (30). The device also has a peripheral circuit region, in which a multiplicity of transistors (21) is formed, for application in a peripheral circuit. The device also has (1) a pair of gate electrode layers (6a, 6b) which are parallel to each other, and at a predetermined distance apart in the memory cell array region, where each pair is part of a transistor (20); (2) a gate electrode layer (6b) and a dummy wiring layer (6d) which are parallel to each other and at a predetermined distance apart in the peripheral circuit region and are part of the transistor (21) for use in the peripheral circuit. The distance between the gate electrode layers (6a, 6b) formed in pairs in the memory cell array region is about the same as the distance between the gate electrode layer (6b) and the dummy wiring layer (6d) in the peripheral circuit region.

Basic Abstract Text - ABTX (2):

Fabricating device comprises (a) forming a conductive layer (6) on the

semiconductor substrate and forming a resist layer (40) on the conductive layer; (b) removing the resist (40), leaving a section of the latter on the conductive layer which is to be used to form the gate electrode layer (6b) and the dummy wiring layer; (c) structuring the conductive layer (6) by etching, using the remaining sections of resist as a mask, and removing the remaining resist sections.

Derwent Accession Number - NRAN (1):
1992-160403

Equivalent Abstract Text - ABEQ (2):

The memory device comprises a pair of parallel gate electrodes each pair constituting a transistor. A second gate electrode layer and a dummy wiring layer at a predetermined spacing constitute the second transistor for use in the peripheral circuit.

Equivalent Abstract Text - ABEQ (3):

The spacing between the paired gate electrode layers is approx. the same as the spacing between the dummy wiring layer and the second gate electrode layer.